



T410H 4A TRIACs

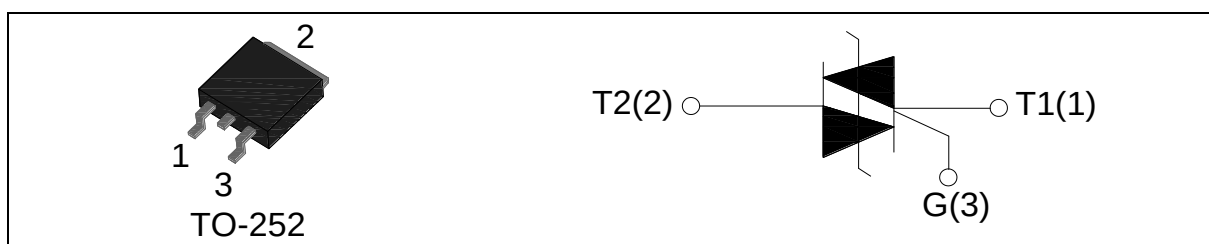
Rev.1.0

DESCRIPTION:

T410H provide high dv/dt rate with strong resistance to electromagnetic interface. They are especially recommended for use on home appliances such as washing machines, and for use on industrial control systems like electromagnetic valves.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	4	A
I_{GT1-3}	10	mA
V_{DRM}/V_{RRM}	800	V



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	°C
Operating junction temperature range		T_j	-40-125	°C
Repetitive peak off-state voltage($T_j=25^{\circ}C$)		V_{DRM}	800	V
Repetitive peak reverse voltage($T_j=25^{\circ}C$)		V_{RRM}	800	V
Non repetitive surge peak Off-state voltage		V_{DSM}	$V_{DRM} +100$	V
Non repetitive peak reverse voltage		V_{RSM}	$V_{RRM} +100$	V
RMS on-state current	TO-252 ($T_C=112^{\circ}C$)	$I_{T(RMS)}$	4	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I_{TSM}	40	A
I^2t value for fusing ($t_p=10ms$)		I^2t	8	A^2s
Rate of rise of on-state current ($I_G=2 \times I_{GT}$)		di/dt	50	A/ μs
Peak gate current		I_{GM}	4	A
Average gate power dissipation		$P_{G(AV)}$	1	W
Peak gate power		P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value	Unit
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	I - II -III	MAX	10	mA
V_{GT}		I - II -III	MAX	1.3	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^{\circ}\text{C } R_L=3.3\text{K}\Omega$	I - II -III	MIN	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III	MAX	20	mA
		II		40	
I_H	$I_T=100\text{mA}$		MAX	15	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^{\circ}\text{C}$		MIN	700	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=6\text{A } t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.5	V
I_{DRM}	$V_D=V_{DRM} \ V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	0.5	mA

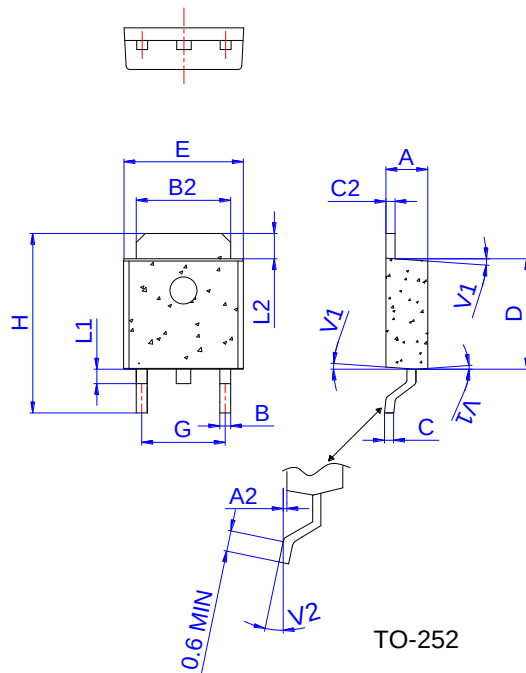
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-252	4.5	$^{\circ}\text{C/W}$

ORDERING INFORMATION

T Triacs	4 $I_{T(RMS)}:4\text{A}$ $I_{GT1-3}\leq 10\text{mA}$	10	H H:High temperature junction	8 $8:V_{DRM} / V_{RRM}\geq 800\text{V}$	K K:TO-252
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PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	4.40		4.70	0.173		0.185
H	9.35		10.6	0.368		0.417
L1	1.30		1.70	0.051		0.067
L2	1.37		1.50	0.054		0.059
V1		4°			4°	
V2	0°		8°	0°		8°

FIG.1: Maximum power dissipation versus RMS on-state current

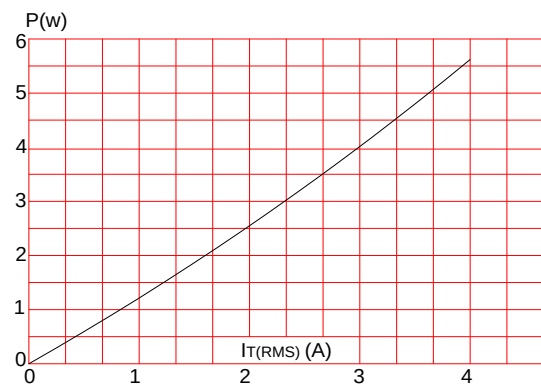


FIG.3: Surge peak on-state current versus number of cycles

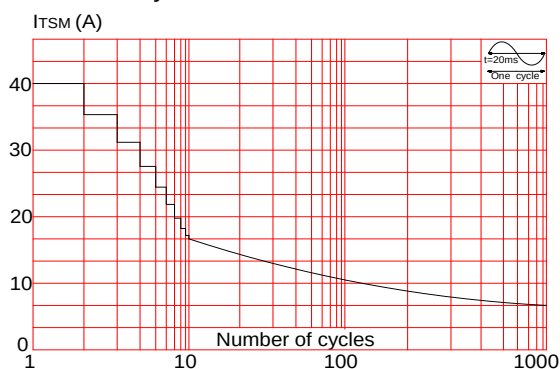


FIG.2: RMS on-state current versus case temperature

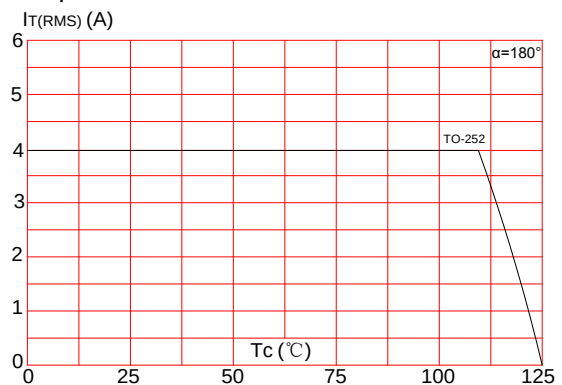


FIG.4: On-state characteristics (maximum values)

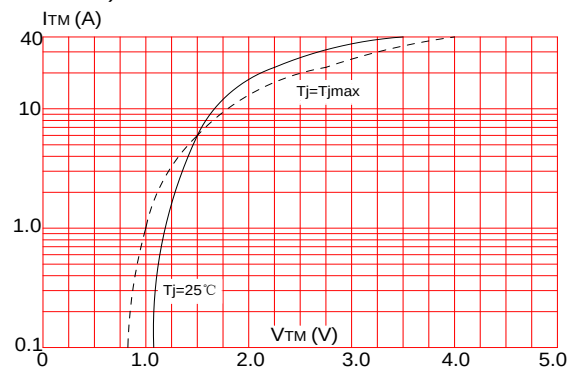


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$ and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

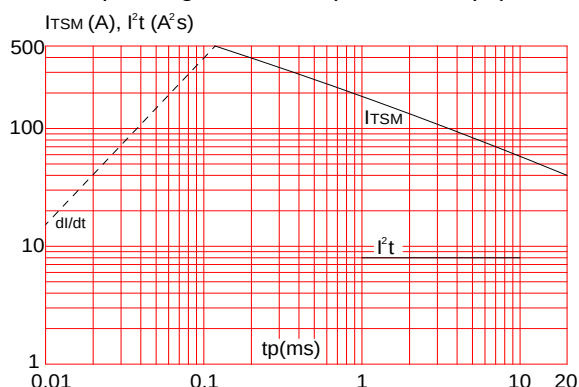
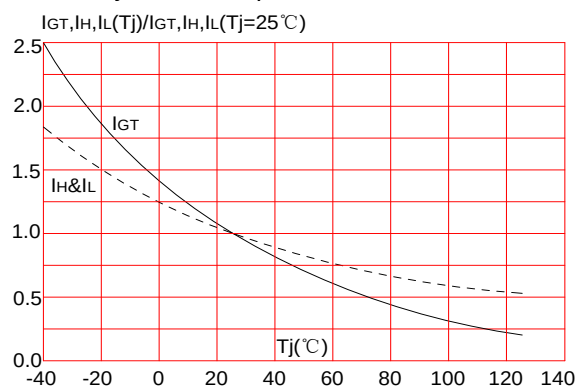


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



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